

Freescale Semiconductor Errata (or Chip Errata)

MMPF0100 Errata for Mask 1N47F and 1N18J

Introduction

Device Revision Identification

This errata document applies to the mask 1N47F, 1N18J SMARTMOS devices.

Table 1. Device Revision Identification

| Part Number | Package | Version | Product Marking | Die ID |
|----------------|--|---------|-----------------|--------------|
| MMPF0100NPEP | | PF0100 | MMPF0100NPEP | 1N47F |
| MMPF0100F0EP | | | MMPF0100F0EP | |
| MMPF0100F1EP | 56 QFN 8x8 mm - | | MMPF0100F1EP | |
| MMPF0100F2EP | 0.5 mm pitch E-Type QFN (full lead) | | MMPF0100F2EP | |
| MMPF0100F3EP | | | MMPF0100F3EP | |
| MMPF0100F4EP | | | MMPF0100F4EP | |
| MMPF0100NPAEP | | PF0100A | MMPF0100NPAEP | |
| MMPF0100F0AEP | | | MMPF0100F0AEP | |
| MMPF0100F1AEP | 56 QFN 8x8 mm - | | MMPF0100F1AEP | |
| MMPF0100F2AEP | 0.5 mm pitch E-Type QFN (full lead) | | MMPF0100F2AEP | |
| MMPF0100F3AEP | | | MMPF0100F3AEP | |
| MMPF0100F4AEP | | | MMPF0100F4AEP | |
| MMPF0100NPANES | | | MMPF0100NPANES | |
| MMPF0100F0ANES | 56 QFN 8x8 mm - 0.5 mm pitch | | MMPF0100F0ANES | |
| MMPF0100F3ANES | WF-Type QFN (wettable flank) | | MMPF0100F3ANES | |
| MMPF0100F4ANES | | | MMPF0100F4ANES | |

Device Part Number Prefixes

Some device samples are marked with a PM prefix. A PM prefix indicates a prototype device which has undergone basic testing only. After full characterization and qualification, devices will be marked with the MM prefix.

General Description

This errata document applies to MMPF0100 series.

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Table 2. Definitions of Errata Severity

| Errata Level | Meaning |
|--------------|---|
| High | Failure mode that severely inhibits the use of the device for all or a majority of intended applications. |
| Medium | Failure mode that might restrict or limit the use of the device for all or a majority of intended applications. |
| Low | Unexpected behavior that does not cause significant problems for the intended applications of the device. |
| Enhancement | Improvement made to the device due to previously found issues on the design. |



Table 3. Errata for the MMPF0100

| Errata No. | Erratum | Customer Impact | Desc | cription | |
|---------------|--|---|------|---|--|
| Medium | Medium Severity | | | | |
| ER19 | Startup: False start and/or non-start of regulators | When VIN starts, it ramps up from between 100 mV and 400 mV, the regulators may not startup and/or the buck regulator outputs can glitch high momentarily. Description: In applications without a valid voltage on the LICELL when VIN starts its ramp from between 100 mV and 4 there can be two failure symptoms: 1 Fuses may not load during startup for systems with VDDOTP = 0 V (OTP configuration) resulting in nor all PF0100 regulators. 2 During VIN ramp up, the top P-MOSFET of buck regmay turn on while 1.0 V ≤ V _{IN} ≤ 2.1 V. For VIN rise less than 10 ms, buck regulator outputs can rise up as VIN transitions from 1.0 V to 2.1 V. For VIN rise greater than 10 ms, buck regulator outputs can ris 2.1 V as VIN transitions from 1.0 V to 2.1 V. Workaround: The workaround consists of external components. Refigure 1. • LDO: 1.3 V to 1.5 V LDO. NCP508 or similar. The should have an enable threshold of 0.9 V or lesset turn on time in the order of 10 μs. • Didde: BAS116 or similar. Didde is not required if the cell is present at LICELL. Only one 1.0 μF is required if of used. Notes: 1. Previously SIP21106, LX8211, MIC5205 or similar were suggested as workaround. While these will prevent symptom 1) mentioned above, they may not prevent symptom 2) since their enable threshold is above 1.0 Applies to: Fix Plan/Status PF0100 Fixed on PF0100A | | n between 100 mV and 400 mV, otoms: g startup for systems with iguration) resulting in non-start of op P-MOSFET of buck regulators $V_{IN} ≤ 2.1$ V. For VIN rise times ulator outputs can rise up to 1.0 V 0 V to 2.1 V. For VIN rise times regulator outputs can rise up to 0 m 1.0 V to 2.1 V. external components. Refer to NCP508 or similar. The LDO reshold of 0.9 V or lesser and a f 10 μs. Diode is not required if no coin Only one 1.0 μF is required if no 211, MIC5205 or similar LDOs nd. While these will prevent e, they may not prevent e threshold is above 1.0 V. Fix Plan/Status | |
| | PF0100 VIN VIN VIN VIN VIN VIN VIN VIN | | | | |



Table 3. Errata for the MMPF0100

| Errata No. | Erratum | Customer Impact | Desci | ription |
|---------------|--|--|---|--------------------|
| Low Sev | verity | | | |
| | VGEN2: VGEN2 current limit not functional at VIN1 < 2.0 V. | No current limit or short circuit protection for VGEN2 at VIN1 < 2.0 V. | Description:For VIN1 < 2.0 V, current limit of VGEN2 LDO is higher than specification. The interrupt bit does not set in case of a fault.Workaround: VIN1 > 2.0 V | |
| ER20 | | | | |
| | | | Applies to: | Fix Plan/Status |
| | | | PF0100 | Fixed on PF0100A |
| | SW1A/B and SW3A/B Regulators: Current sharing is not equal for SW1A/B and SW3A/B in dual | Output ripple may be higher than specification at load currents greater than 1.25 A. | Description: The output ripple may be higher than specification at load currents greater than 1.25 A due to unequal current sharing between the two phases. | |
| ER21 | phase mode. Workaround: Do not use SW1A/B and SW3A/I configuration. | | A/B in the dual phase | |
| | | | Applies to: | Fix Plan/Status |
| | | | PF0100, PF0100A | No fix scheduled |
| | RESETBMCU: RESETBMCU fault mode generates a false fault signal when SWBST is used. | When SWBST is used without load in the AUTO mode, RESETBMCU may go low and trigger a false fault. | Description: When RESETBMCU is in fault mode (OTP_PG_EN bit = 1) and SWBST operates at light loads in AUTO mode, the SWBST inductor current may be limited by internal circuitry resulting in a false RESETBMCU signal. | |
| | | | The erratum does not apply if | SWBST is not used. |
| ER22 | | | Workaround: There are two workarounds for this erratum. | |
| ERZZ | | | Do not turn on SWBST in the OTP sequence. Change operating mode of SWBST to APS before turning it on via software. Replace the 2.2 μH inductor with a 4.7 μH on SWBST. | |
| | | | Applies to: | Fix Plan/Status |
| | | | PF0100 | Fixed on PF0100A |



Revision History

| Revision | Date | Description |
|----------|---------|--|
| 1.0 | 10/2012 | Initial release |
| 2.0 | 2/2013 | Updated ER19 Change Fix plan/Status of ER19, R20 and ER22 to be fixed in next silicon revision. |
| 3.0 | 7/2013 | Added MMPF0100A and SMPF0100A devices ER20, and ER22 fixed on PF0100A |
| 4.0 | 12/2013 | Added MMPF0100AN and SMPF0100AN Extended Industrial parts. ER19, ER20 and ER22 fixed on PF0100A |
| 5.0 | 4/2014 | Updated Device Revision Identification table Included SW1A/B in ER21 |





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